

<b>INFORMATION DISCLOSURE PRECIPITATION RPO-1449</b>	Atty. Docket No. 032206	Serial No.: 10/743,793
	Applicant(s): Katsuto TANAHASHI, et al.	
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### U.S. PATENT DOCUMENTS

Examiner Initial	Document No.	Name	Date	Class	Subclass	Filing Date (If appropriate)
<i>[Signature]</i>	U.S. 4,885,257	Matsushita	12/5/1989	437	11	June 2, 1987
<i>[Signature]</i>	U.S. 6,277,501 B1	Fujikawa	8/21/2001	428	641	August 21, 2001

### FOREIGN PATENT DOCUMENTS

Examiner Initial	Document No.	Date	Country	Translation (Yes or No)
<i>[Signature]</i>	60-31231	2/18/1985	JP	Yes-Abstract (See U.S. Pat. 4,885,257)
<i>[Signature]</i>	10-50715	2/20/1998	JP	Yes-Abstract (see U.S. Pat. 6,277,501B1)
<i>[Signature]</i>	11-204534	7/30/1999	JP	Yes-Abstract & Partial English Translation Claim 1
<i>[Signature]</i>	2002-208596A	7/26/2002	JP	Yes-Abstract & Partial English Translation Claim 1-3
<i>[Signature]</i>	2000-72595A	3/7/2000	JP	Yes-Abstract
<i>[Signature]</i>	10-229,093A	8/25/1998	JP	Yes-Abstract

### OTHER DOCUMENTS

<i>[Signature]</i>  <i>[Signature]</i>  <i>[Signature]</i>	M.J. Binns, et al., "The Control of Boron Autodoping During Device Processing For P/P+ EPI Wafers With No Back-Surface Oxide Seal, Electrochemical Society Proceedings, Volume 2002-2, pp. 682-693, May 12, 2002.	
	M. Inaba and H. Daneda, "Low-temperature IR absorption measurement for Oxygen Precipitation in Heavily Doped Substrate, Process Development Div., Fujitsu Ltd., The 57 <sup>th</sup> Meeting of The Japan Society of Applied Physics and Related Societies Extended Abstracts, 7p-ZG-5, 1996.	
	Y. Shirakawa et al., "Annealing Behavior of Carbon-Oxygen Complexes in Silicon Crystals Observed By Low-temperature Infrared Absorption", J. Applied Physics 77, pp. 41-46, January 1, 1995.	
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Date Considered		<i>[Signature]</i> 06/12/05